The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-2. (Canceled)

3. (Currently Amended) A manufacturing method for a semiconductor device, comprising:

forming at least first and second semiconductor layers that are divided from each other in an island-like shape over a substrate having an insulating surface, wherein each of said first and second semiconductor layers includes a region to become at least a channel region of a thin film transistor;

forming a conductive layer covering an entire surface of each of the first and second semiconductor layers with an insulating layer interposed therebetween; and

selectively heating the first and second semiconductor layers by irradiating an incoherent electromagnetic wave within a wavelength band ranging at least from a visible light band to an infrared band to thereby conduct heat treatment on each of the first and second semiconductor layers and the insulating [[layer]] layer,

wherein said conductive layer extends beyond each periphery of the first and second semiconductor layers at least when the selective heating of the first and second semiconductor layers is performed.

4. (Currently Amended) The method according to claim 3 further comprising a step of etching the conductive layer after the selective heating of the first and second semiconductor layers to form at least first and second gate electrodes over the first and second semiconductor ~~islands~~ layers, respectively.

5. (Previously Presented) The method according to claim 3 wherein said incoherent electromagnetic wave is irradiated for 30 to 300 seconds.

6.-7. (Canceled)

8. (Previously Presented) A manufacturing method for a semiconductor device according to claim 3, wherein the substrate is a glass substrate.

9.-12. (Canceled)

13. (Previously Presented) A manufacturing method for a semiconductor device according to claim 3, wherein the substrate is selected from one of quartz and sapphire.

14.-17. (Canceled)

18. (Previously Presented) A manufacturing method for a semiconductor device according to claim 3, wherein the substrate has a transmittance of 50 % or higher with respect to the electromagnetic wave within the wavelength band.

19.-22. (Canceled)

23. (Previously Presented) A manufacturing method for a semiconductor device according to claim 3, wherein the conductive layer comprises a metal nitride.

24.-27. (Canceled)

28. (Original) A manufacturing method for a semiconductor device according to claim 3, further comprising forming a second conductive layer on the conductive layer and forming a part of a gate electrode using the conductive layer.

29.-32. (Canceled)

33. (Previously Presented) A manufacturing method for a semiconductor device according to claim 3, wherein the selective heating of the substrate is performed at a temperature not lower than a distortion point of the substrate.

34.-35. (Canceled)

36. (Original) A manufacturing method for a semiconductor device, comprising:

heating an entire surface of a substrate by radiation heating from a first heat source;

forming non-transparent layers that are separated from each other in an island-like shape over the substrate, the non-transparent layers each having a different, higher absorptance with respect to an incoherent electromagnetic wave within a wavelength band ranging at least from a visible light band to an infrared band, than the substrate; and

locally heating a region where each of the non-transparent layers having the high absorptance with respect to the incoherent electromagnetic wave is formed, by using a second heat source for radiating the incoherent electromagnetic wave.

37. (Original) A manufacturing method for a semiconductor device, comprising:

heating an entire surface of a substrate by radiation heating from a first heat source;

forming a non-transparent layer to overlap with a semiconductor layer formed in an island-like shape through an insulating film over the substrate, the non-transparent layer having a different, higher absorptance with respect to an incoherent electromagnetic wave within a wavelength band ranging at least from a visible light band to an infrared band, than the substrate; and

selectively heating a region where the non-transparent layer having the high absorptance with respect to the incoherent electromagnetic wave is formed, by using a second heat source for radiating the incoherent electromagnetic wave to thereby conduct heat treatment on the semiconductor layer and the insulating layer through conductive heating from the non-transparent layer having the high absorptance with respect to the electromagnetic wave.

38. (Previously Presented) A manufacturing method for a semiconductor device according to claim 36, wherein the substrate is a glass substrate.

39. (Previously Presented) A manufacturing method for a semiconductor device according to claim 37, wherein the substrate is a glass substrate.

40. (Previously Presented) A manufacturing method for a semiconductor device according to claim 36, wherein the substrate is selected from one of quartz and sapphire.

41. (Previously Presented) A manufacturing method for a semiconductor device according to claim 37, wherein the substrate is selected from one of quartz and sapphire.

42. (Previously Presented) A manufacturing method for a semiconductor device according to claim 36, wherein the substrate has a transmittance of 50 % or higher with respect to the electromagnetic wave within the wavelength band.

43. (Previously Presented) A manufacturing method for a semiconductor device according to claim 37, wherein the substrate has a transmittance of 50 % or higher with respect to the electromagnetic wave within the wavelength band.

44. (Canceled)

45. (Previously Presented) A manufacturing method for a semiconductor device according to claim 37, wherein the insulating layer covers a top surface and a side surface of each of the semiconductor layers.

46. (Canceled)

47. (Previously Presented) A manufacturing method for a semiconductor device according to claim 37, wherein the insulating layer includes a laminate of a silicon oxide film and a silicon nitride film.

48. (Original) A manufacturing method for a semiconductor device according to claim 36, wherein the non-transparent layer having the high absorptance is formed of a high melting-point metal selected from the group consisting of molybdenum (Mo), tungsten (W), titanium (Ti), and chromium (Cr).

49. (Original) A manufacturing method for a semiconductor device according to claim 37, wherein the non-transparent layer having the high absorptance is formed of a

high melting-point metal selected from the group consisting of molybdenum (Mo), tungsten (W), titanium (Ti), and chromium (Cr).

50. (Original) A manufacturing method for a semiconductor device according to claim 36, wherein the non-transparent layer having the high absorptance is formed of a metal nitride selected from the group consisting of titanium nitride (TiN), tantalum nitride (TaN), and tungsten nitride (WN).

51. (Original) A manufacturing method for a semiconductor device according to claim 37, wherein the non-transparent layer having the high absorptance is formed of a metal nitride selected from the group consisting of titanium nitride (TiN), tantalum nitride (TaN), and tungsten nitride (WN).

52. (Original) A manufacturing method for a semiconductor device according to claim 36, wherein the non-transparent layer having the high absorptance is formed of one selected from the group consisting of tungsten silicide (WSi_2), molybdenum silicide ($MoSi_2$), titanium silicide ($TiSi_2$), tantalum silicide ($TaSi_2$), chromium silicide ($CrSi_2$), cobalt silicide ($CoSi_2$), and platinum silicide ($PtSi_2$).

53. (Original) A manufacturing method for a semiconductor device according to claim 37, wherein the non-transparent layer having the high absorptance is formed of one selected from the group consisting of tungsten silicide (WSi_2), molybdenum silicide ($MoSi_2$), titanium silicide ($TiSi_2$), tantalum silicide ($TaSi_2$), chromium silicide ($CrSi_2$), cobalt silicide ($CoSi_2$), and platinum silicide ($PtSi_2$).

54. (Original) A manufacturing method for a semiconductor device according to claim 36, wherein the substrate has a transmittance of 60% or higher with respect to the incoherent electromagnetic wave within the wavelength band ranging from the visible

light band to the infrared band and the non-transparent layer having the high absorptance has a transmittance of 30% or lower with respect to the incoherent electromagnetic wave within the wavelength band ranging from the visible light band to the infrared band.

55. (Original) A manufacturing method for a semiconductor device according to claim 37, wherein the substrate has a transmittance of 60% or higher with respect to the incoherent electromagnetic wave within the wavelength band ranging from the visible light band to the infrared band and the non-transparent layer having the high absorptance has a transmittance of 30% or lower with respect to the incoherent electromagnetic wave within the wavelength band ranging from the visible light band to the infrared band.

56. (Original) A manufacturing method for a semiconductor device according to claim 36, wherein the second heat treatment step is performed at a temperature not lower than a distortion point of the substrate.

57. (Original) A manufacturing method for a semiconductor device according to claim 37, wherein the second heat treatment step is performed at a temperature not lower than a distortion point of the substrate.

58.-73. (Canceled)

74. (Currently Amended) A manufacturing method for a semiconductor device, comprising:

forming a semiconductor layer over a substrate;

forming an insulating layer over the semiconductor layer wherein said semiconductor layer includes a region to become at least a channel region of a thin film transistor;

forming a conductive layer over the semiconductor layer with the insulating layer interposed therebetween; and

selectively heating the semiconductor layer by using a heat source capable of radiating an incoherent electromagnetic wave within a wavelength band ranging at least from a visible light band to an infrared [[band]] band,

wherein said conductive layer extends beyond a periphery of the semiconductor layer at least when the selective heating of the semiconductor layer is performed.

75. (Previously Presented) A manufacturing method for a semiconductor device according to claim 74, wherein a transparency of said substrate with respect to said incoherent electromagnetic wave is 50% or larger.

76. (Previously Presented) A manufacturing method for a semiconductor device according to claim 74, wherein said substrate is a glass substrate.

77. (Previously Presented) A manufacturing method for a semiconductor device according to claim 74, wherein said substrate is selected from one of quartz and sapphire.

78. (Previously Presented) A manufacturing method for a semiconductor device according to claim 74, wherein the conductive layer comprises a metal nitride.

79. (Previously Presented) A manufacturing method for a semiconductor device according to claim 74, further comprising forming a second conductive layer on the conductive layer for forming at least a part of a gate electrode.

80. (Previously Presented) A manufacturing method for a semiconductor device according to claim 74, wherein the selective heating of the semiconductor layer is performed at a temperature not lower than a distortion point of the substrate.

81. (New) A manufacturing method for a semiconductor device according to claim 74, further comprising a step of etching the conductive layer after the selective heating of the semiconductor layer to form a gate electrode over the semiconductor layer.